



ECH8601M

N-Channel Power MOSFET 24V, 8A, 23mΩ, Dual ECH8

ON Semiconductor®

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Features

- Low ON-resistance
- 2.5V drive
- Common-drain type
- Protection diode in
- Built-in gate protection resistor
- Best suited for LiB charging and discharging switch
- Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

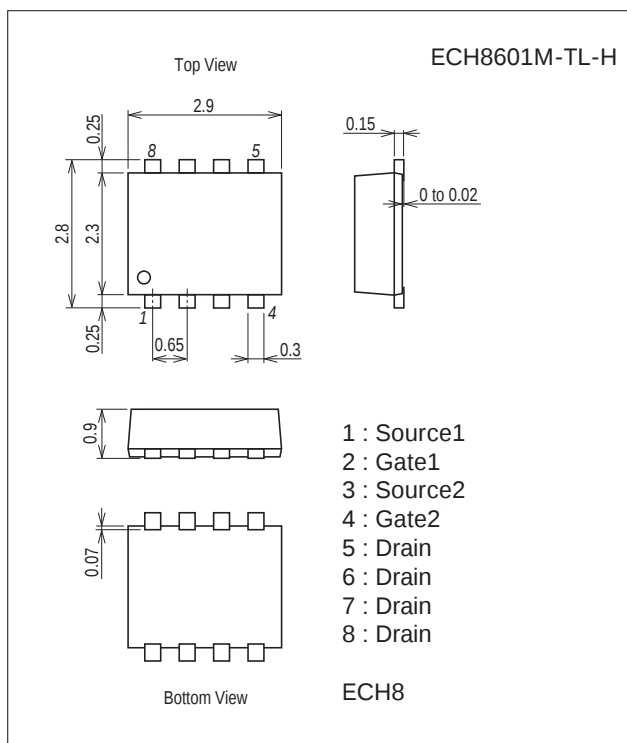
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		24	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	I _D		8	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	60	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (1000mm ² ×0.8mm) 1unit	1.5	W
Total Dissipation	P _T	When mounted on ceramic substrate (1000mm ² ×0.8mm)	1.6	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

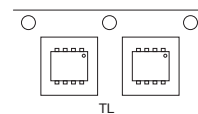
7011A-003



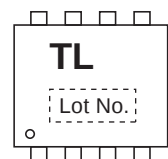
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

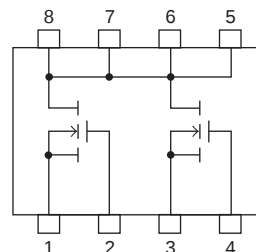
Packing Type : TL



Marking



Electrical Connection

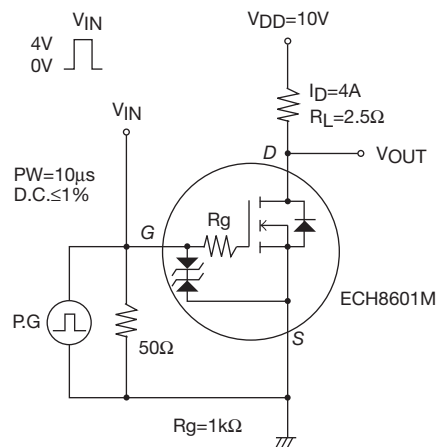


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Electrical Characteristics at Ta=25°C

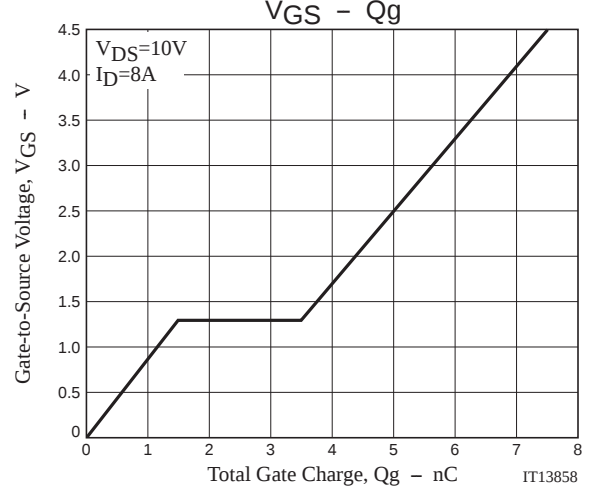
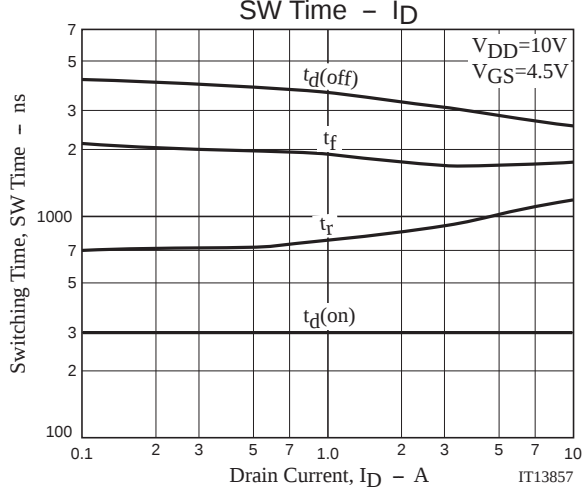
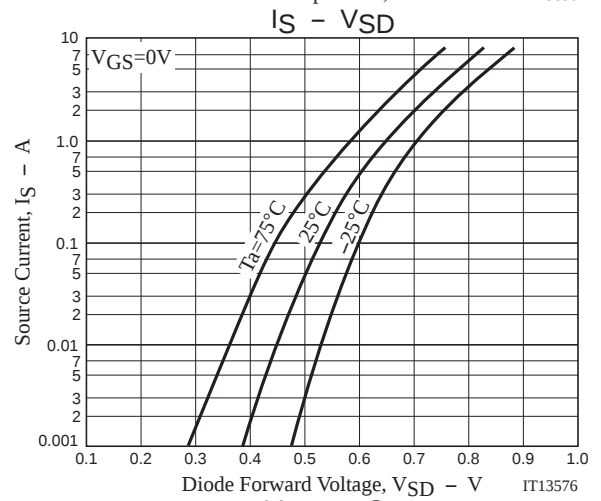
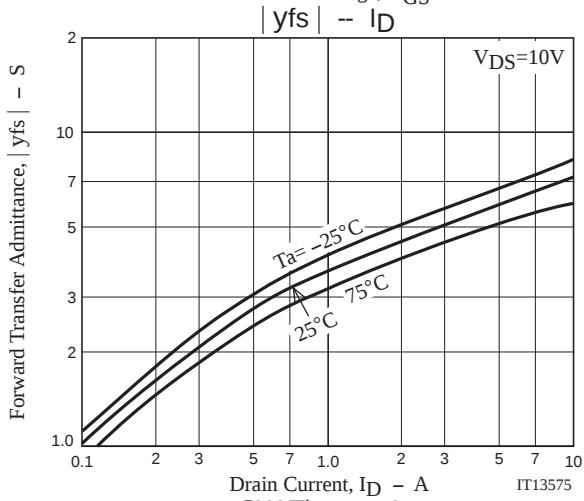
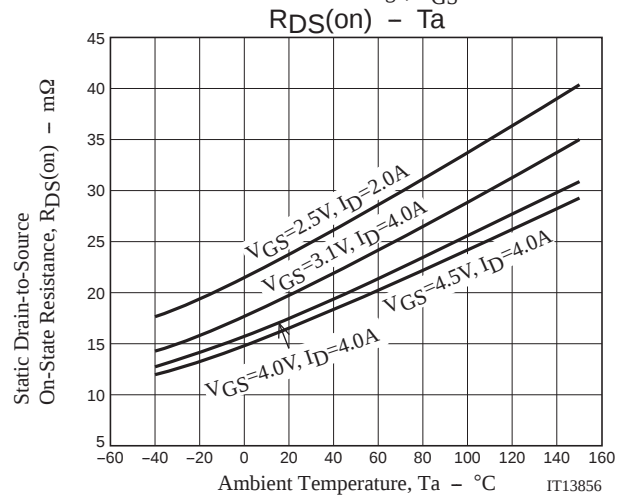
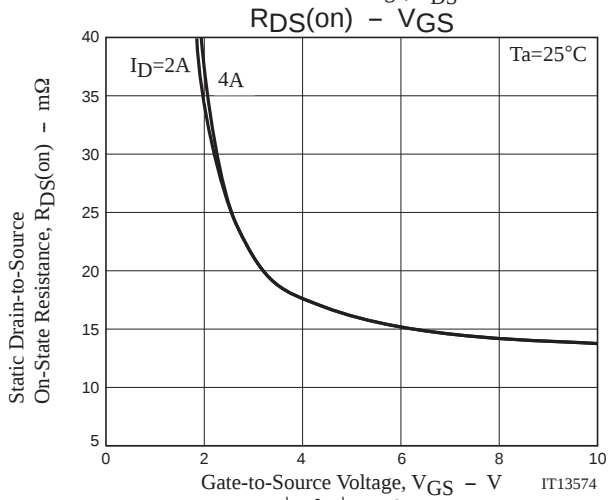
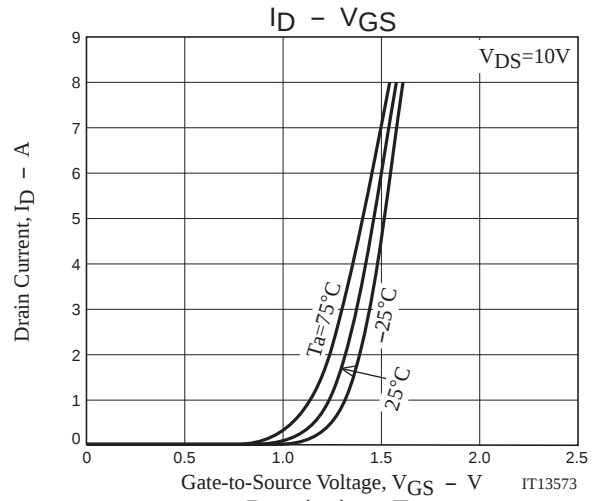
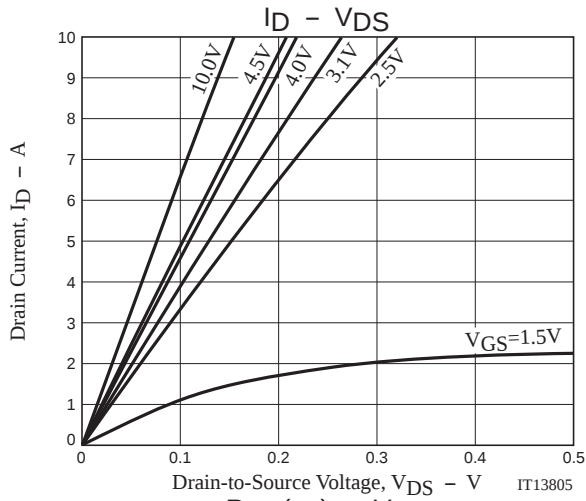
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	24			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=4A$	3.1	5.3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=4A, V_{GS}=4.5V$	13.5	17	23	$m\Omega$
	$R_{DS(on)2}$	$I_D=4A, V_{GS}=4.0V$	14	18	24	$m\Omega$
	$R_{DS(on)3}$	$I_D=4A, V_{GS}=3.1V$	14.5	20	30	$m\Omega$
	$R_{DS(on)4}$	$I_D=2A, V_{GS}=2.5V$	16	24	35	$m\Omega$
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		300		ns
Rise Time	t_r			1000		ns
Turn-OFF Delay Time	$t_{d(off)}$			3000		ns
Fall Time	t_f			1800		ns
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V, I_D=8A$		7.5		nC
Gate-to-Source Charge	Q_{gs}			1.5		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2.0		nC
Diode Forward Voltage	V_{SD}	$I_S=8A, V_{GS}=0V$		0.8	1.2	V

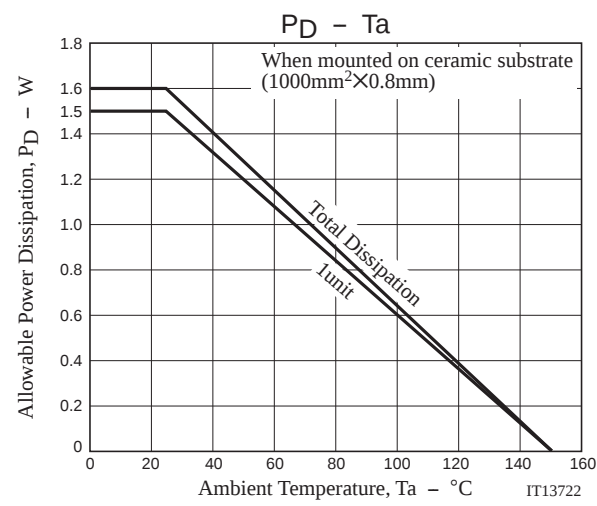
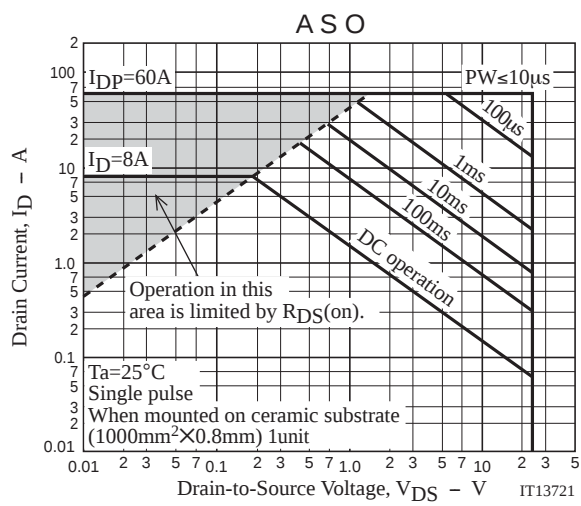
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
ECH8601M-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free

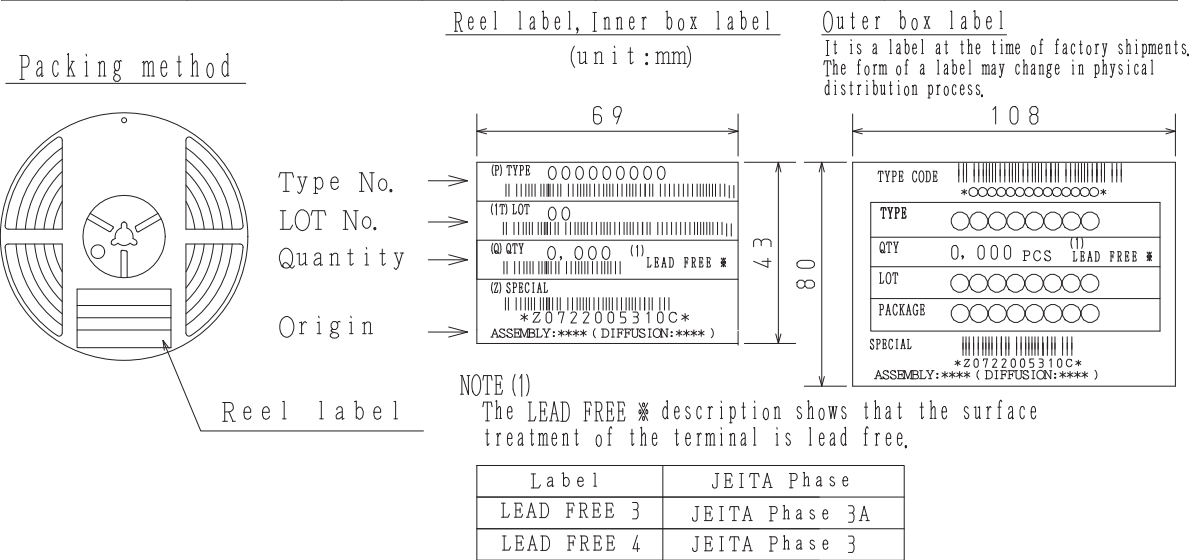




Embossed Taping Specification
ECH8601M-TL-H

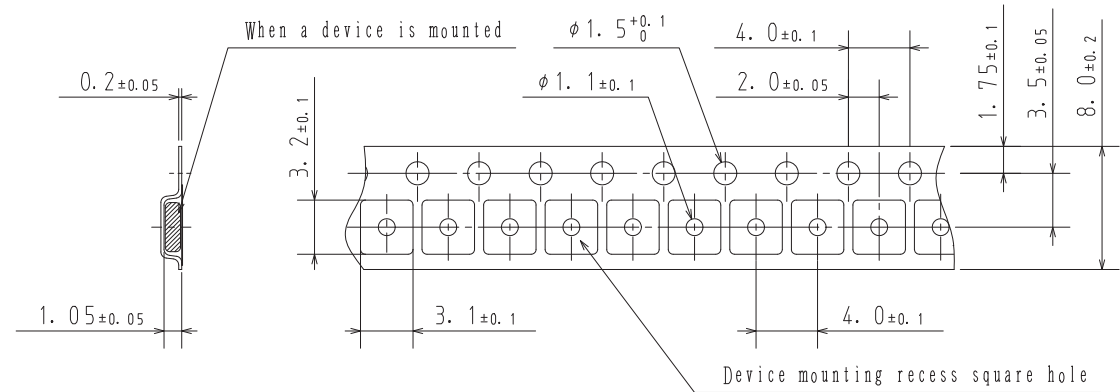
1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

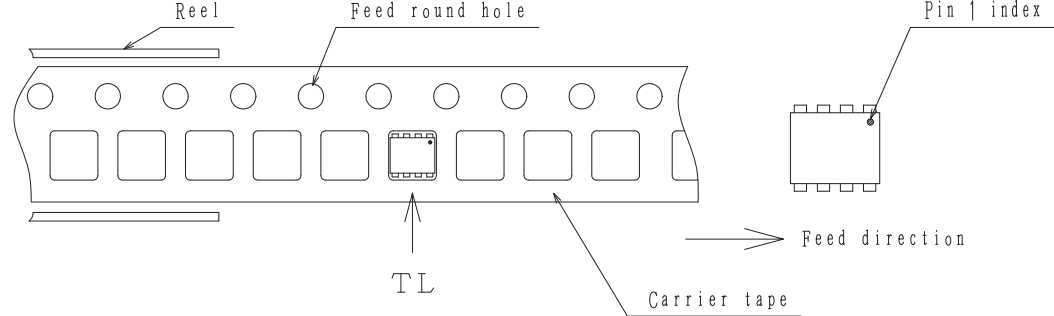


2. Taping configuration

2-1. Carrier tape size (unit:mm)



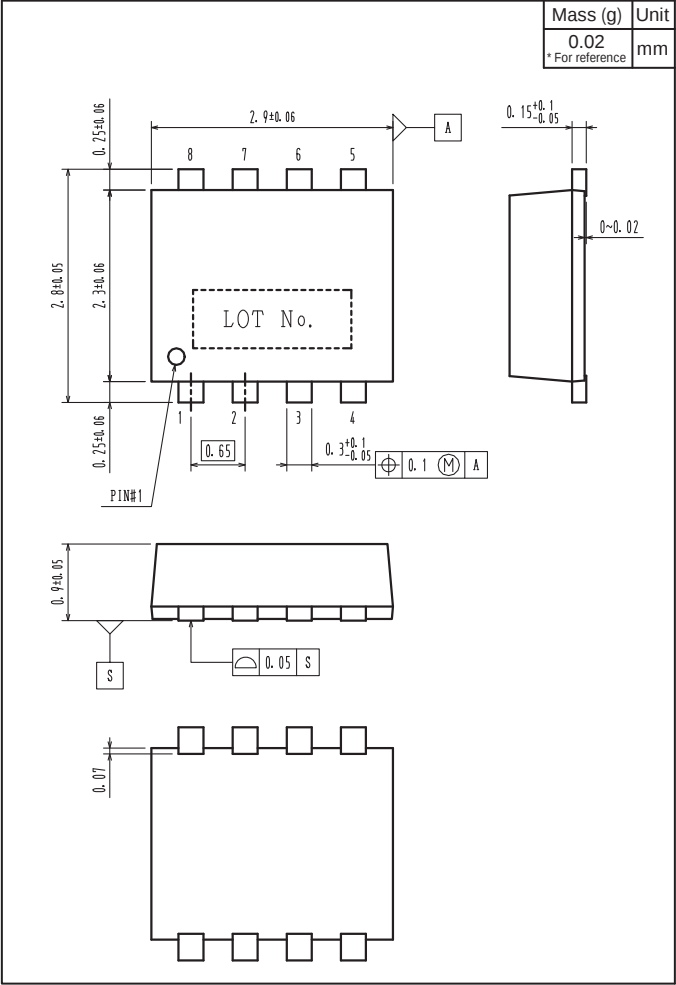
2-2. Device placement direction



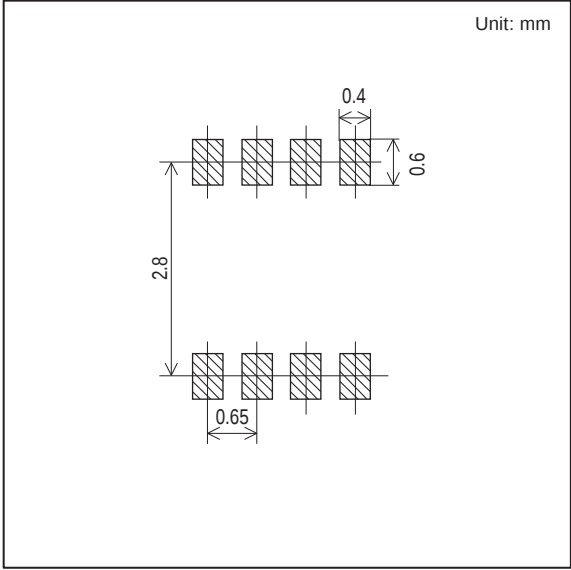
Those with pin 1 index on the feed hole side.....TL

Outline Drawing

ECH8601M-TL-H



Land Pattern Example



Note on usage : Since the ECH8601M is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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